

MS1227

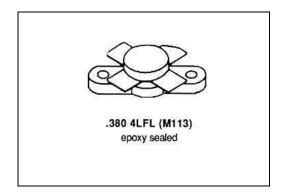
RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS

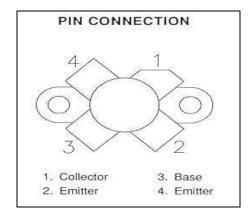
Features

- 30 MHz
- 12.5 VOLTS
- GOLD METALIZATION
- P_{OUT} = 20 W MINIMUM
- G_P = 15 dB
- COMMON EMITTER CONFIGURATION

DESCRIPTION:

The MS1227 is a 12.5V epitaxial NPN planar transistor designed primarily for SSB communications. This device utilizes emitter ballasting for improved ruggedness and reliability.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	36	٧
V _{CEO}	Collector-Emitter Voltage	18	V
V _{EBO}	Emitter-Base Voltage	4.0	V
Ic	Device Current	4.5	Α
P _{DISS}	Power Dissipation	80	W
TJ	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

R _{TH(J-C)}	Junction-case Thermal Resistance	2.2	°C/W
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ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

Symbol	Test Conditions			Value		
			Min.	Typ.	Max.	Unit
BVcbo	$I_C = 50mA$	I _E = 0mA	36			V
Bvces	$I_C = 50mA$	V _{BE} = 0V	36			V
Bvceo	$I_C = 50mA$	I _B = 0mA	18			V
Bvebo	$I_E = 5mA$	$I_C = 0mA$	4.0			V
Ices	V _{CB} = 15V	I _E = 0mA			5	mA
H _{FE}	V _{CE} = 5V	I _C = 1A	10		200	

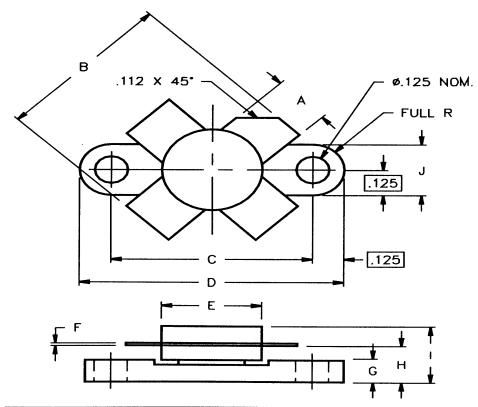
DYNAMIC

Symbol		Test Conditions	3		Value		
				Min.	Typ.	Max.	Unit
P _{out}	f = 30MHz	$V_{CC} = 12.5V$	$I_{CQ} = 25mA$	20			W
G _P	f = 30MHz	V _{CC} = 12.5V	I _{CQ} = 25mA	15			dB
IMD	f = 30MHz	V _{CC} = 12.5V	I _{CQ} = 25mA			-30	dB
Cob	f = 1 MHz	$V_{CB} = 30V$				135	pf





PACKAGE MECHANI CAL DATA



	Мимим	MUMIXAM		MUMINIM	MAXIMUM
	INCHES/MM	INCHES/MM		INCHES/MM	INCHES/MM
Α	.220/5,59	.230/5,84	1		.260/7,11
В	.785/19,94		J	.240/6,10	.255/6,48
С	.720/18,29	.730/18,54			
D	.970/24,64	.980/24,89			
Ε		.385/9,78			
F	.004/0,10	.006/0,15			
G	.085/2,16	.105/2,67			
Н	.160/4,06	.180/4,57			